



## ELC-505-34

LED Chip vis

ELC-505-34

Rev. 01 aus 2011

Radiation	Type	Electrodes
green		P + N up

	<p>Description</p> <ul style="list-style-type: none"> <li>-Substrate: Sapphire, epitaxial layer: GaN based Material</li> <li>-N bonding pad electrode: Au alloy</li> <li>-P bonding pad electrode: Au alloy</li> </ul> <p>Above drawing is not on real scale</p>
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### Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		$I_F$			20	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$	$I_{FM}$			100	mA

### Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20\text{mA}$	$V_F$		3.3	3.5	V
Reverse current	$V_R = 5\text{V}$	$I_R$			1	$\mu\text{A}$
Dominant wavelength	$I_F = 20\text{mA}$	$\lambda_p$	502	505	508	nm
Full width at half maximum	$I_F = 20\text{mA}$	$\Delta\lambda$		40		nm
Luminous intensity <sup>1</sup>	$I_F = 20\text{mA}$	$I_v$	300		500	mcd

### Packing

Chips on adhesive film with wire-bond side top

